

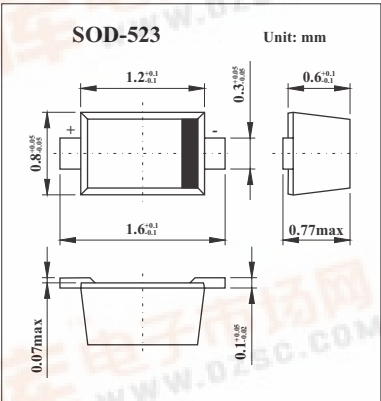
SMD Type

Diodes

Silicon Epitaxial Trench Pin Diode
HVC135

■ Features

- Adopting the trench structure improves low capacitance.(C=0.6pF max)
- Low forward resistance. (rf=2.0 Ω max)
- Low operation current.



■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Value	Unit
Peak reverse voltage	VRM	65	V
Reverse voltage	VR	60	V
Forward current	IF	100	mA
Power dissipation	Pd	150	mW
Junction temperature	Tj	125	℃
Storage temperature	Tstg	-55 to +125	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current	IR	VR = 60 V			0.1	μA
Reverse voltage	VF	IF = 2 mA			0.9	V
Capacitance	C	VR = 1 V, f = 1 MHz			0.6	pF
Forward resistance	rf	IF = 2 mA, f = 100 MHz			2.0	Ω
ESD-Capability *1		C =200pF, Both forward and reverse direction 1 pulse	100			V

Note

1. Failure criterion ; IR > 100 nA at VR = 60V.

■ Marking

Marking	P5
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